NCE N-Channel Enhancement Mode Power MOSFET

Description

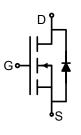
The NCE1502R uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

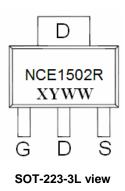
- V_{DS} = 150V, I_D = 2A $R_{DS(ON)}$ < 300mΩ @ V_{GS} =10V (Typ:260mΩ)
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Excellent package for good heat dissipation

Application

- Power switching application
- Hard switched and high frequency circuits



Schematic diagram



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE1502R	NCE1502R	SOT-223-3L	Ø330mm	12mm	2500 units

Absolute Maximum Ratings (T_A=25 ℃unless otherwise noted)

Absolute maximum ratings (14-20 cumess otherwise noted)						
Parameter	Symbol	Limit	Unit			
Drain-Source Voltage	VDS	150	V			
Gate-Source Voltage	Vgs	±20	V			
Drain Current-Continuous	I _D	2	Α			
Drain Current-Pulsed (Note 1)	I _{DM}	6	Α			
Maximum Power Dissipation	P _D	2	W			
Operating Junction and Storage Temperature Range	$T_{\rm J}, T_{\rm STG}$	-55 To 150	$^{\circ}$			

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{ hetaJA}$	62.5	°C/W

Electrical Characteristics (T_A=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	150	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =150V,V _{GS} =0V	-	-	1	μA



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NCE1502R

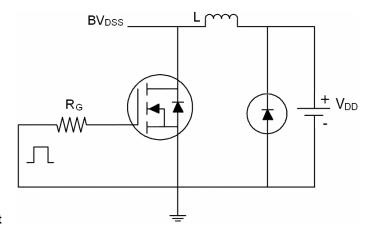
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA	
On Characteristics (Note 3)							
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =250μA	1.5	2.0	2.5	V	
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =1.5A	-	260	300	mΩ	
Forward Transconductance	G FS	V _{DS} =15V,I _D =1.5A	-	3	-	S	
Dynamic Characteristics (Note4)							
Input Capacitance	C _{lss}	- V _{DS} =25V,V _{GS} =0V,	-	235	-	PF	
Output Capacitance	C _{oss}	- V _{DS} -25V,V _{GS} -0V, - F=1.0MHz	-	36	-	PF	
Reverse Transfer Capacitance	C _{rss}	F-1.UIVITZ	-	20	-	PF	
Switching Characteristics (Note 4)							
Turn-on Delay Time	t _{d(on)}		-	8	-	nS	
Turn-on Rise Time	t _r	V_{DD} =75 V , I_{D} =1 A , R_{L} =75 Ω	-	10	-	nS	
Turn-Off Delay Time	$t_{d(off)}$	V_{GS} =10 V , R_{G} =6 Ω	-	20	-	nS	
Turn-Off Fall Time	t _f		-	15	-	nS	
Total Gate Charge	Q_g	\/ -75\/ -1.5\	-	8		nC	
Gate-Source Charge	Q_{gs}	- V _{DS} =75V,I _D =1.5A, - V _{GS} =10V	-	1.4	-	nC	
Gate-Drain Charge	Q _{gd}	V _{GS} -10V	-	2.1	-	nC	
Drain-Source Diode Characteristics							
Diode Forward Voltage (Note 3)	V_{SD}	V _{GS} =0V,I _S =2A	-	-	1.2	V	
Diode Forward Current (Note 2)	I _S		-	-	2	Α	

Notes:

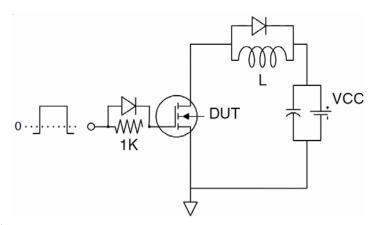
- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- **3.** Pulse Test: Pulse Width ≤ 300μ s, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to product

Test Circuit

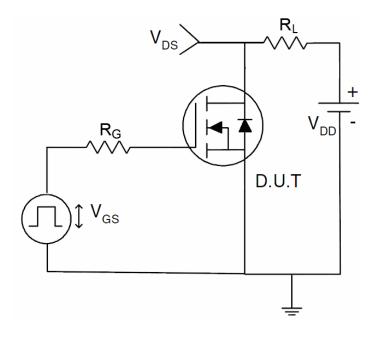
1) E_{AS} Test Circuit



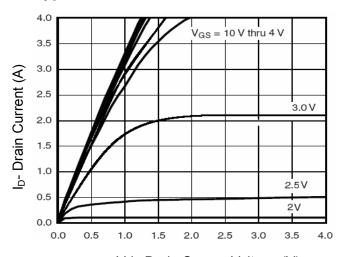
2) Gate Charge Test Circuit



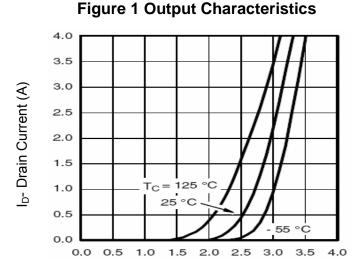
3) Switch Time Test Circuit



Typical Electrical and Thermal Characteristics (Curves)



Vds Drain-Source Voltage (V)



Vgs Gate-Source Voltage (V)

Figure 2 Transfer Characteristics

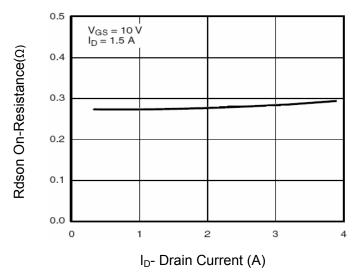


Figure 3 Rdson- Drain Current

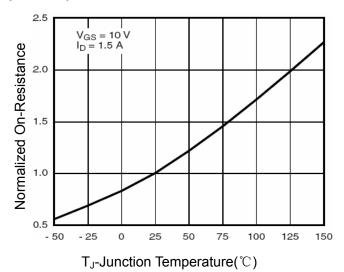
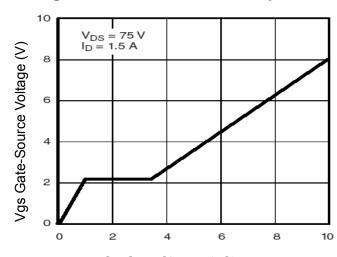


Figure 4 Rdson- Junction Temperature



Qg Gate Charge (nC)
Figure 5 Gate Charge

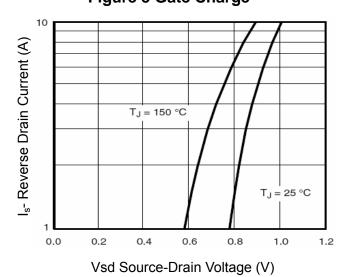


Figure 6 Source- Drain Diode Forward

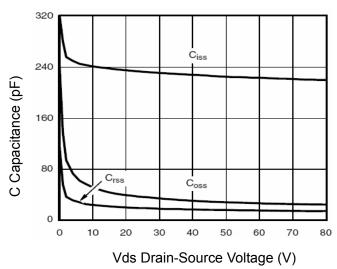
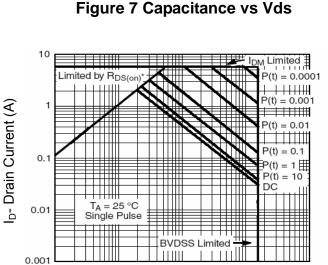


Figure 7 Capacitance vs Vds



Vds Drain-Source Voltage (V)

0.1

Figure 8 Safe Operation Area

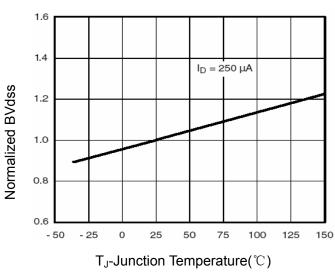
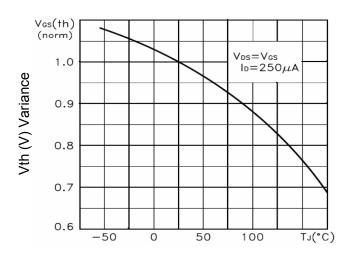


Figure 9 BV_{DSS} vs Junction Temperature



 T_J -Junction Temperature($^{\circ}$ C)

Figure 10 V_{GS(th)} vs Junction Temperature

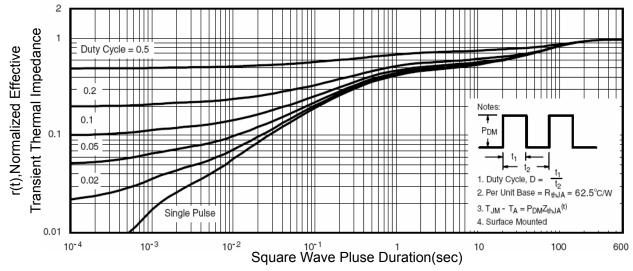
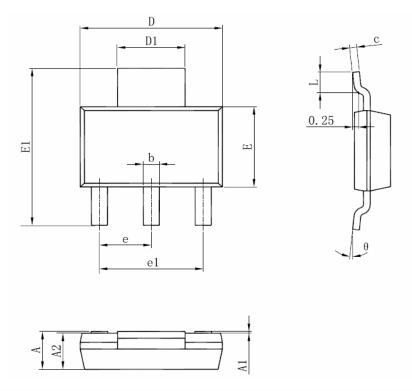


Figure 11 Normalized Maximum Transient Thermal Impedance

SOT-223-3L Package Information



Coumb a I	Dimensions Ir	n Millimeters	Dimensions In Inches		
Symbol	Min	Max	Min	Max	
Α	1.520	1.800	0.060	0.071	
A1	0.000	0.100	0.000	0.004	
A2	1.500	1.700	0.059	0.067	
b	0.660	0.820	0.026	0.032	
С	0.250	0.350	0.010	0.014	
D	6.200	6.400	0.244	0.252	
D1	2.900	3.100	0.114	0.122	
E	3.300	3.700	0.130	0.146	
E1	6.830	7.070	0.269	0.278	
е	2.300	(BSC)	0.091(BSC)	
e1	4.500	4.700	0.177	0.185	
L	0.900	1.150	0.035	0.045	
θ	0°	10°	0°	10°	

Notes

- 1. All dimensions are in millimeters.
- 2. Tolerance ±0.10mm (4 mil) unless otherwise specified
- 3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
- 4. Dimension L is measured in gauge plane.
- $5. \ Controlling \ dimension \ is \ millimeter, \ converted \ inch \ dimensions \ are \ not \ necessarily \ exact.$

Pb-Free Product

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